



RF Power Field Effect Transistors

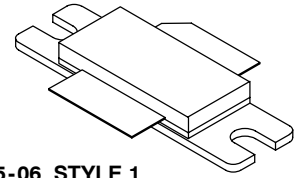
N-Channel Enhancement-Mode Lateral MOSFETs

Designed for PCN and PCS base station applications with frequencies from 2100 to 2200 MHz. Suitable for W-CDMA, CDMA, TDMA, GSM and multicarrier amplifier applications.

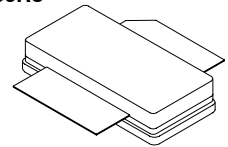
- Typical W-CDMA Performance: 2140 MHz, 28 Volts
 5 MHz Offset @ 4.096 MHz BW, 15 DTCH
 Output Power — 6.0 Watts
 Power Gain — 12.5 dB
 Drain Efficiency — 15%
- Internally Matched, Controlled Q, for Ease of Use
- High Gain, High Efficiency and High Linearity
- Integrated ESD Protection
- Designed for Maximum Gain and Insertion Phase Flatness
- Capable of Handling 10:1 VSWR, @ 28 Vdc, 2110 MHz, 60 Watts CW Output Power
- Excellent Thermal Stability
- Characterized with Series Equivalent Large-Signal Impedance Parameters
- In Tape and Reel. R3 Suffix = 250 Units per 56 mm, 13 Inch Reel.

MRF21060R3
MRF21060SR3

2170 MHz, 60 W, 28 V
LATERAL N-CHANNEL
RF POWER MOSFETs



CASE 465-06, STYLE 1
NI-780
MRF21060R3



CASE 465A-06, STYLE 1
NI-780S
MRF21060SR3

Table 1. Maximum Ratings

Rating	Symbol	Value	Unit
Drain-Source Voltage	V_{DSS}	-0.5, +65	Vdc
Gate-Source Voltage	V_{GS}	-0.5, +15	Vdc
Total Device Dissipation @ $T_C = 25^\circ\text{C}$ Derate above 25°C	P_D	180 0.98	W W/ $^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 65 to +150	$^\circ\text{C}$
Operating Junction Temperature	T_J	200	$^\circ\text{C}$

Table 2. Thermal Characteristics

Characteristic	Symbol	Value	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	1.02	$^\circ\text{C}/\text{W}$

Table 3. ESD Protection Characteristics

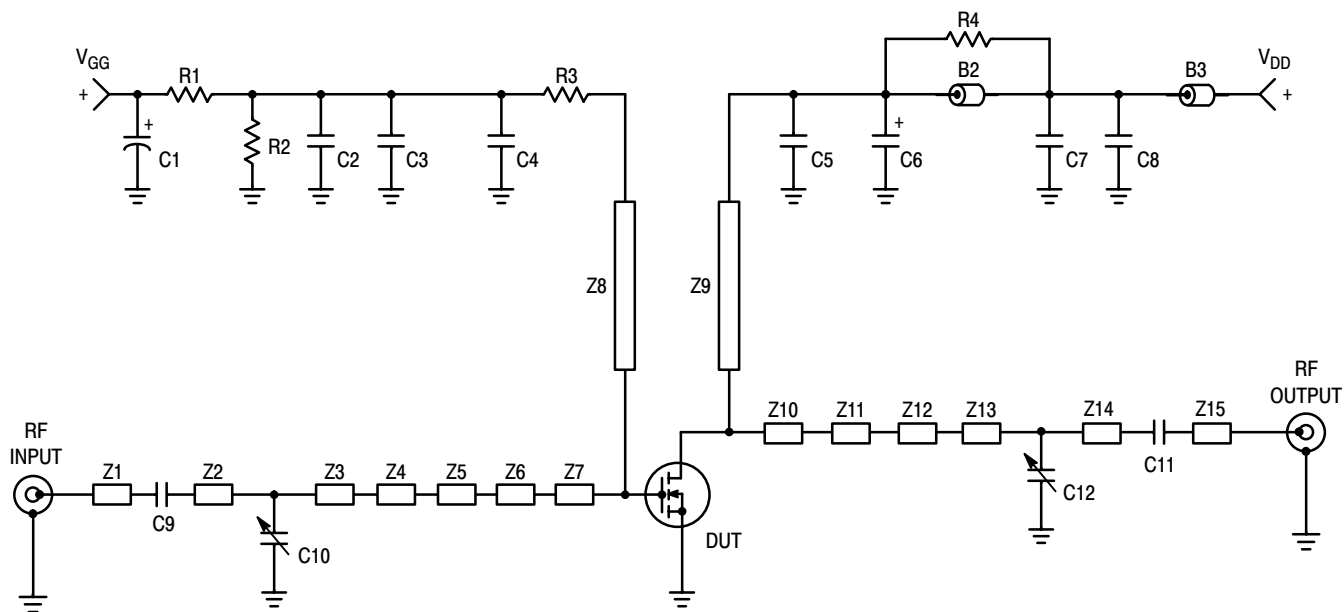
Test Conditions	Class
Human Body Model	2 (Minimum)
Machine Model	M3 (Minimum)

NOTE - CAUTION - MOS devices are susceptible to damage from electrostatic charge. Reasonable precautions in handling and packaging MOS devices should be observed.

Table 4. Electrical Characteristics ($T_C = 25^\circ\text{C}$ unless otherwise noted)

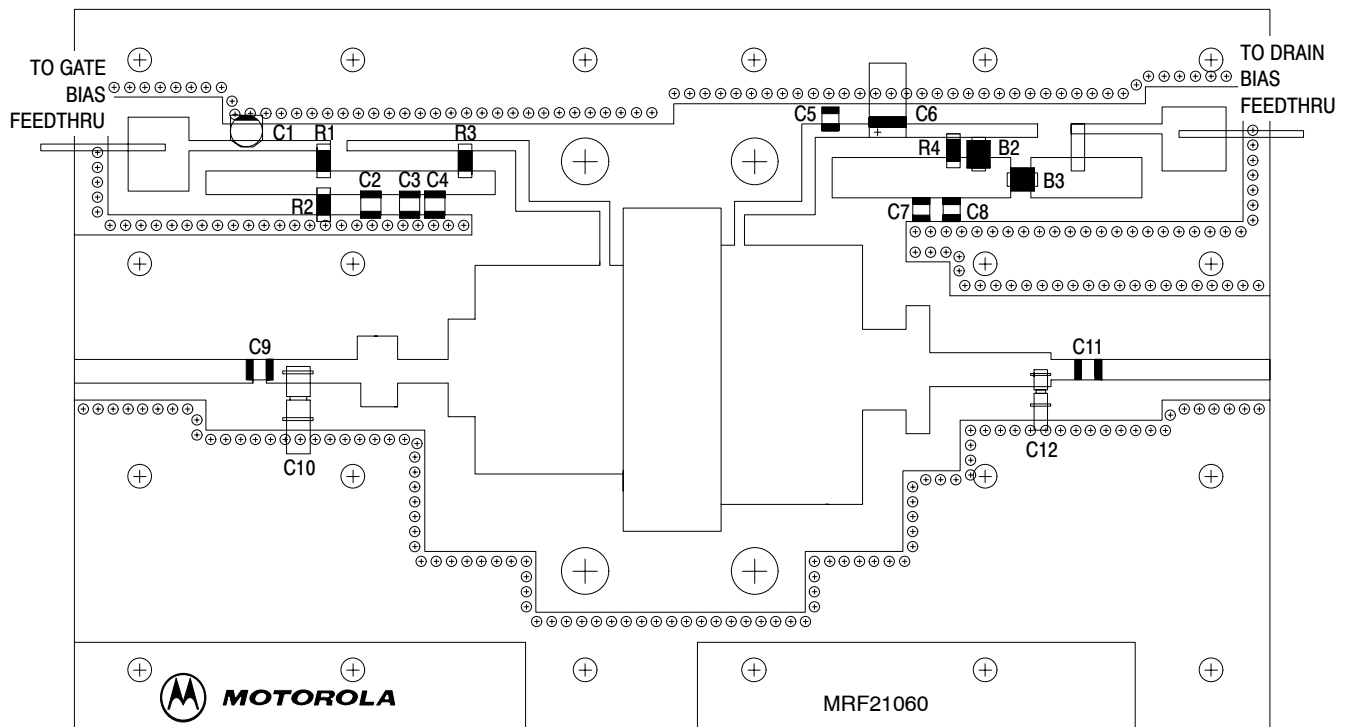
Characteristic	Symbol	Min	Typ	Max	Unit
Off Characteristics					
Drain-Source Breakdown Voltage ($V_{GS} = 0\text{ Vdc}$, $I_D = 10\ \mu\text{Adc}$)	$V_{(BR)DSS}$	65	—	—	Vdc
Zero Gate Voltage Drain Current ($V_{DS} = 28\text{ Vdc}$, $V_{GS} = 0\text{ Vdc}$)	I_{DSS}	—	—	6	μAdc
Gate-Source Leakage Current ($V_{GS} = 5\text{ Vdc}$, $V_{DS} = 0\text{ Vdc}$)	I_{GSS}	—	—	1	μAdc
On Characteristics					
Gate Threshold Voltage ($V_{DS} = 10\text{ Vdc}$, $I_D = 300\ \mu\text{Adc}$)	$V_{GS(th)}$	2	—	4	Vdc
Gate Quiescent Voltage ($V_{DS} = 28\text{ Vdc}$, $I_D = 500\text{ mAdc}$)	$V_{GS(Q)}$	2.5	3.9	4.5	Vdc
Drain-Source On-Voltage ($V_{GS} = 10\text{ Vdc}$, $I_D = 2\text{ Adc}$)	$V_{DS(on)}$	—	0.27	—	Vdc
Forward Transconductance ($V_{DS} = 10\text{ Vdc}$, $I_D = 2\text{ Adc}$)	g_{fs}	—	4.7	—	S
Dynamic Characteristics					
Reverse Transfer Capacitance (1) ($V_{DS} = 28\text{ Vdc}$, $V_{GS} = 0$, $f = 1\text{ MHz}$)	C_{rss}	—	2.7	—	pF
Functional Tests (In Freescale Test Fixture, 50 ohm system)					
Two-Tone Common-Source Amplifier Power Gain ($V_{DD} = 28\text{ Vdc}$, $P_{out} = 60\text{ W PEP}$, $I_{DQ} = 500\text{ mA}$, $f = 2110\text{ MHz}$ and 2170 MHz , Tone Spacing = 100 kHz)	G_{ps}	11	12.5	—	dB
Two-Tone Drain Efficiency ($V_{DD} = 28\text{ Vdc}$, $P_{out} = 60\text{ W PEP}$, $I_{DQ} = 500\text{ mA}$, $f = 2110\text{ MHz}$ and 2170 MHz , Tone Spacing = 100 kHz)	η	31	34	—	%
3rd Order Intermodulation Distortion ($V_{DD} = 28\text{ Vdc}$, $P_{out} = 60\text{ W PEP}$, $I_{DQ} = 500\text{ mA}$, $f = 2110\text{ MHz}$ and 2170 MHz , Tone Spacing = 100 kHz)	IMD	—	-30	-28	dBc
Input Return Loss ($V_{DD} = 28\text{ Vdc}$, $P_{out} = 60\text{ W PEP}$, $I_{DQ} = 500\text{ mA}$, $f = 2110\text{ MHz}$ and 2170 MHz , Tone Spacing = 100 kHz)	IRL	—	-12	—	dB
$P_{out, 1\text{ dB}}$ Compression Point ($V_{DD} = 28\text{ Vdc}$, $P_{out} = 60\text{ W CW}$, $f = 2170\text{ MHz}$)	P_{1dB}	—	60	—	W
Output Mismatch Stress ($V_{DD} = 28\text{ Vdc}$, $P_{out} = 60\text{ W CW}$, $I_{DQ} = 500\text{ mA}$, $f = 2110\text{ MHz}$, $V_{SWR} = 10:1$, All Phase Angles at Frequency of Tests)	Ψ	No Degradation In Output Power Before and After Test			

1. Part is internally matched both on input and output.



B2 - B3	Ferrite Beads, Fair Rite #2743019447	Z3	0.180" x 0.100" Microstrip
C1	10 μ F, 50 V Electrolytic Chip Capacitor, Panasonic #ECEV1HV100R	Z4	0.152" x 0.293" Microstrip
C2, C7	1000 pF Chip Capacitors, ATC #100B102JCA500X	Z5	0.216" x 0.100" Microstrip
C3, C8	0.10 μ F Chip Capacitors, Kemet #CDR33BX104AKWS	Z6	0.114" x 0.410" Microstrip
C4, C5	4.7 pF Chip Capacitors, ATC #100B4R7JCA500X	Z7	0.626" x 0.872" Microstrip
C6	22 μ F, 35 V Tantalum Surface Mount Chip Capacitor, Sprague	Z8	1.050" x 0.050" Microstrip
C9, C11	9.1 pF Chip Capacitors, ATC #100B9R1JCA500X	Z9	0.830" x 0.050" Microstrip
C10	0.8 pF - 8.0 pF Variable Capacitor, Johanson Gigatrim	Z10	0.596" x 1.040" Microstrip
C12	0.4 pF - 4.5 pF Variable Capacitor, Johanson Gigatrim	Z11	0.186" x 0.315" Microstrip
R1	1 k Ω , 1/4 W Fixed Film Chip Resistor, 0.08" x 0.13"	Z12	0.097" x 0.525" Microstrip
R2	560 k Ω , 1/4 W Fixed Film Chip Resistor, 0.08" x 0.13"	Z13	0.353" x 0.138" Microstrip
R3	10 Ω , 1/4 W Fixed Film Chip Resistor, 0.08" x 0.13"	Z14	0.112" x 0.080" Microstrip
R4	10 Ω , 1/4 W Fixed Film Chip Resistor, 0.08" x 0.13"	Z15	0.722" x 0.080" Microstrip
Z1	0.743" x 0.080" Microstrip	Board	0.030" Glass Teflon [®] , Arlon GX-0300-55-22, 2 oz Cu
Z2	0.070" x 0.100" Microstrip		

Figure 1. MRF21060 Test Circuit Schematic



Freescall has begun the transition of marking Printed Circuit Boards (PCBs) with the Freescall Semiconductor signature/logo. PCBs may have either Motorola or Freescall markings during the transition period. These changes will have no impact on form, fit or function of the current product.

Figure 2. MRF21060 Test Circuit Component Layout

TYPICAL CHARACTERISTICS

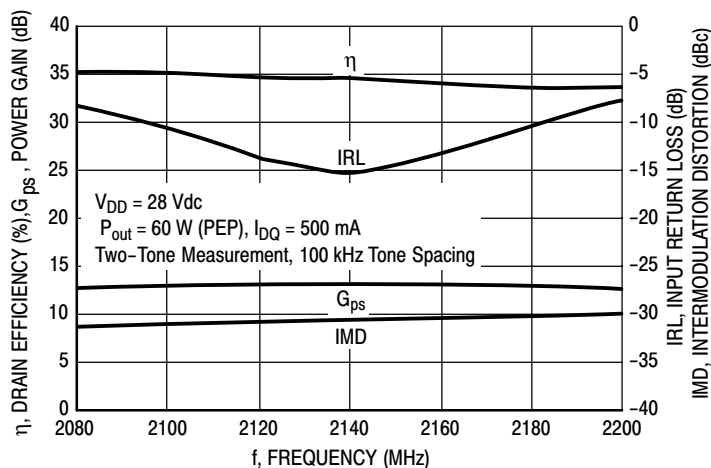


Figure 3. Class AB Broadband Circuit Performance

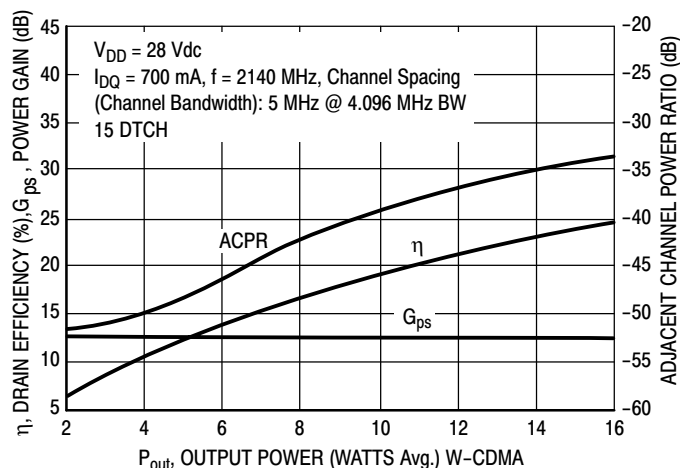


Figure 4. W-CDMA ACPR, Power Gain and Drain Efficiency versus Output Power

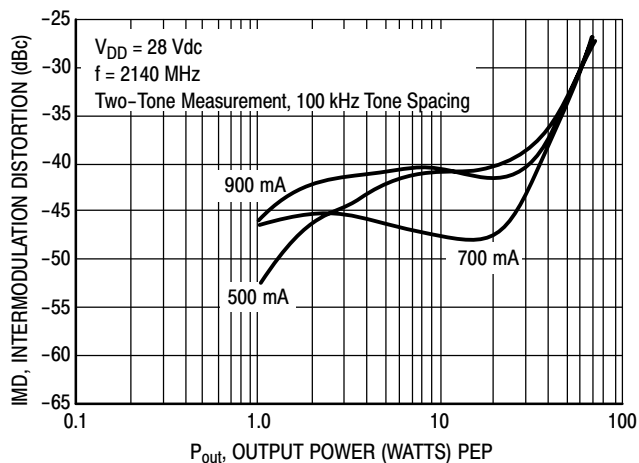


Figure 5. Intermodulation Distortion versus Output Power

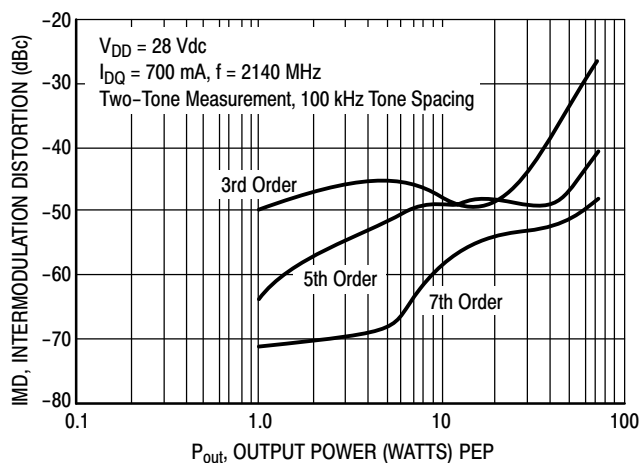


Figure 6. Intermodulation Distortion Products versus Output Power

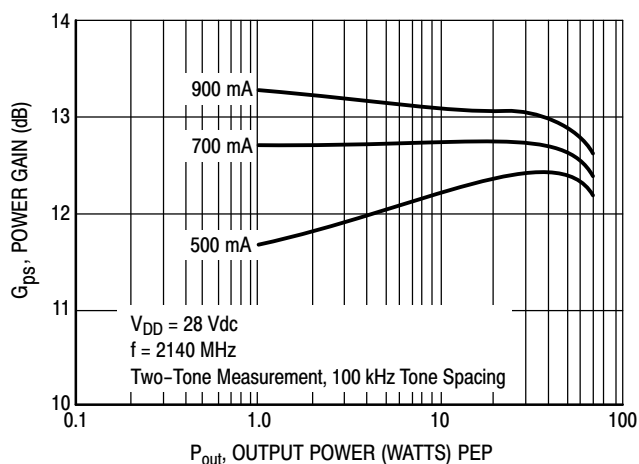


Figure 7. Power Gain versus Output Power

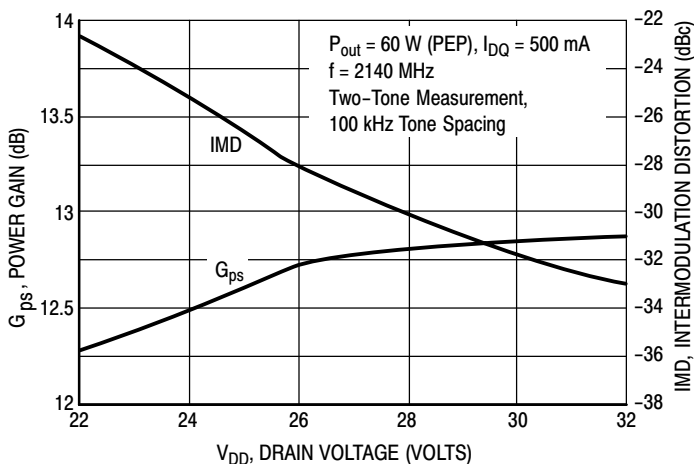
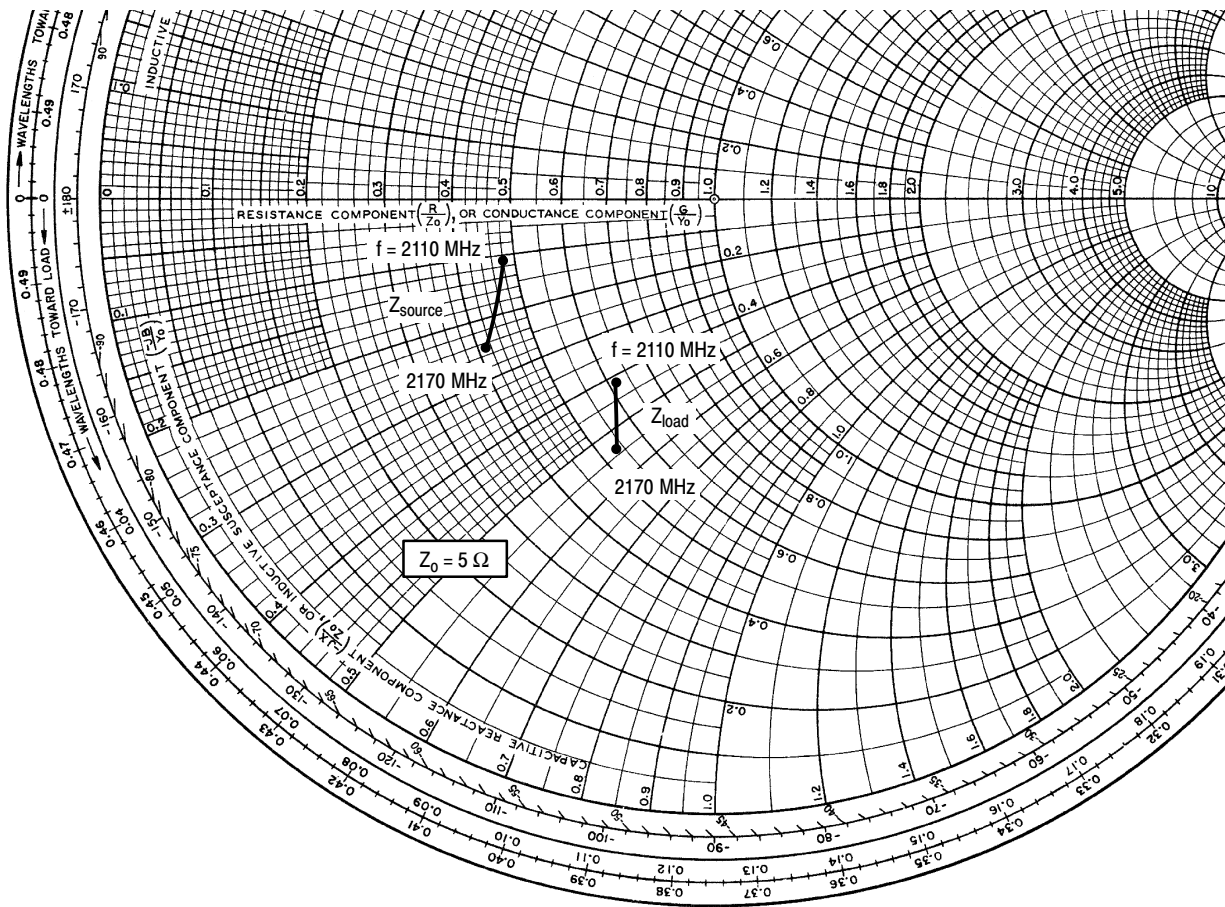


Figure 8. Power Gain and Intermodulation Distortion versus Supply Voltage



$V_{DD} = 28 \text{ V}$, $I_{DQ} = 500 \text{ mA}$, $P_{out} = 60 \text{ W PEP}$

f MHz	Z_{source} Ω	Z_{load} Ω
2110	$2.40 - j0.55$	$3.07 - j2.05$
2140	$2.26 - j0.87$	$2.89 - j2.38$
2170	$2.08 - j1.23$	$2.66 - j2.71$

Z_{source} = Test circuit impedance as measured from gate to ground.

Z_{load} = Test circuit impedance as measured from drain to ground.

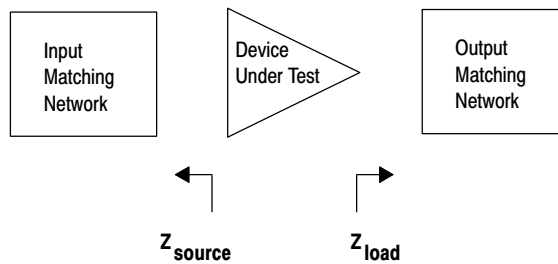
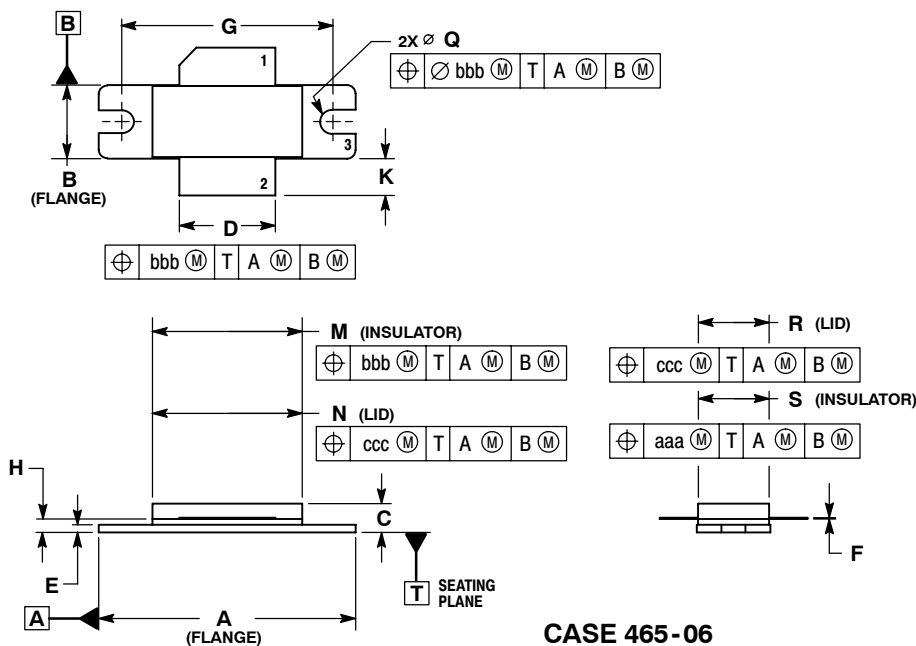


Figure 9. Series Equivalent Source and Load Impedance

PACKAGE DIMENSIONS

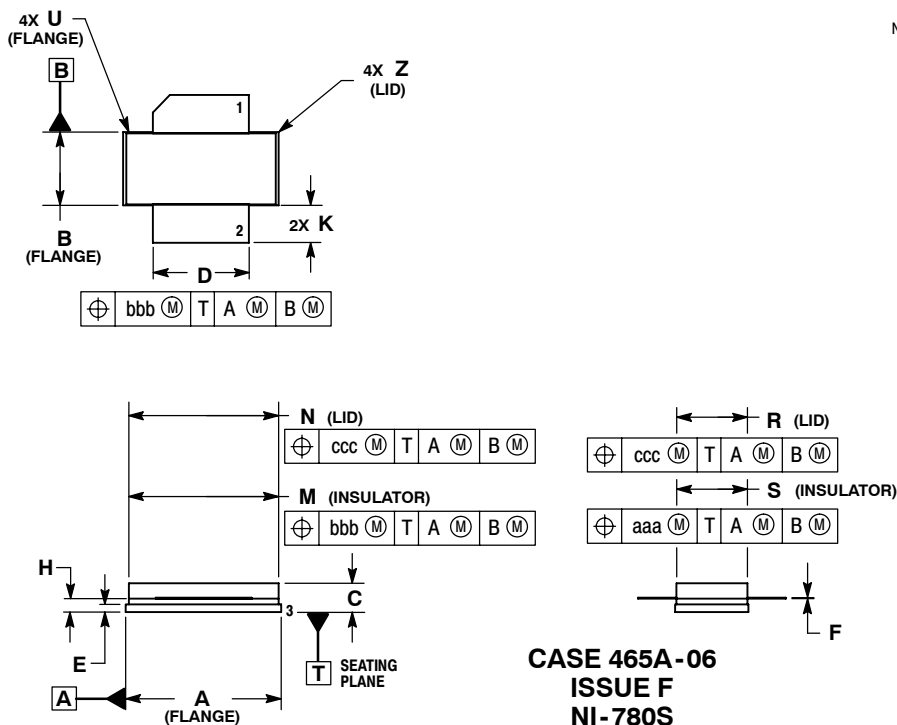


- NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M-1994.
 2. CONTROLLING DIMENSION: INCH.
 3. DELETED
 4. DIMENSION H IS MEASURED 0.030 (0.762) AWAY FROM PACKAGE BODY.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	1.335	1.345	33.91	34.16
B	0.380	0.390	9.65	9.91
C	0.125	0.170	3.18	4.32
D	0.495	0.505	12.57	12.83
E	0.035	0.045	0.89	1.14
F	0.003	0.006	0.08	0.15
G	1.100 BSC		27.94 BSC	
H	0.057	0.067	1.45	1.70
K	0.170	0.210	4.32	5.33
M	0.774	0.786	19.66	19.96
N	0.772	0.788	19.60	20.00
Q	Ø.118	Ø.138	Ø3.00	Ø3.51
R	0.365	0.375	9.27	9.53
S	0.365	0.375	9.27	9.52
aaa	0.005 REF		0.127 REF	
bbb	0.010 REF		0.254 REF	
ccc	0.015 REF		0.381 REF	

- STYLE 1:
PIN 1: DRAIN
2: GATE
3: SOURCE

**CASE 465-06
ISSUE F
NI-780
MRF21060R3**



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DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.805	0.815	20.45	20.70
B	0.380	0.390	9.65	9.91
C	0.125	0.170	3.18	4.32
D	0.495	0.505	12.57	12.83
E	0.035	0.045	0.89	1.14
F	0.003	0.006	0.08	0.15
H	0.057	0.067	1.45	1.70
K	0.170	0.210	4.32	5.33
M	0.774	0.786	19.61	20.02
N	0.772	0.788	19.61	20.02
R	0.365	0.375	9.27	9.53
S	0.365	0.375	9.27	9.52
U	---	0.040	---	1.02
Z	---	0.030	---	0.76
aaa	0.005 REF		0.127 REF	
bbb	0.010 REF		0.254 REF	
ccc	0.015 REF		0.381 REF	

- STYLE 1:
PIN 1: DRAIN
2: GATE
5: SOURCE

**CASE 465A-06
ISSUE F
NI-780S
MRF21060SR3**

How to Reach Us:

Home Page:
www.freescale.com

E-mail:
support@freescale.com

USA/Europe or Locations Not Listed:
Freescale Semiconductor
Technical Information Center, CH370
1300 N. Alma School Road
Chandler, Arizona 85224
+1-800-521-6274 or +1-480-768-2130
support@freescale.com

Europe, Middle East, and Africa:
Freescale Halbleiter Deutschland GmbH
Technical Information Center
Schatzbogen 7
81829 Muenchen, Germany
+44 1296 380 456 (English)
+46 8 52200080 (English)
+49 89 92103 559 (German)
+33 1 69 35 48 48 (French)
support@freescale.com

Japan:
Freescale Semiconductor Japan Ltd.
Headquarters
ARCO Tower 15F
1-8-1, Shimo-Meguro, Meguro-ku,
Tokyo 153-0064
Japan
0120 191014 or +81 3 5437 9125
support.japan@freescale.com

Asia/Pacific:
Freescale Semiconductor Hong Kong Ltd.
Technical Information Center
2 Dai King Street
Tai Po Industrial Estate
Tai Po, N.T., Hong Kong
+800 2666 8080
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